

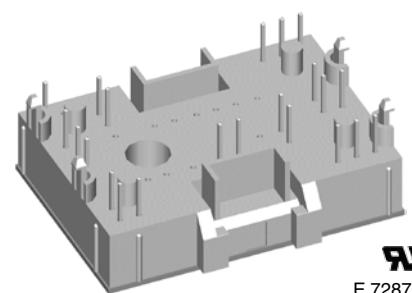
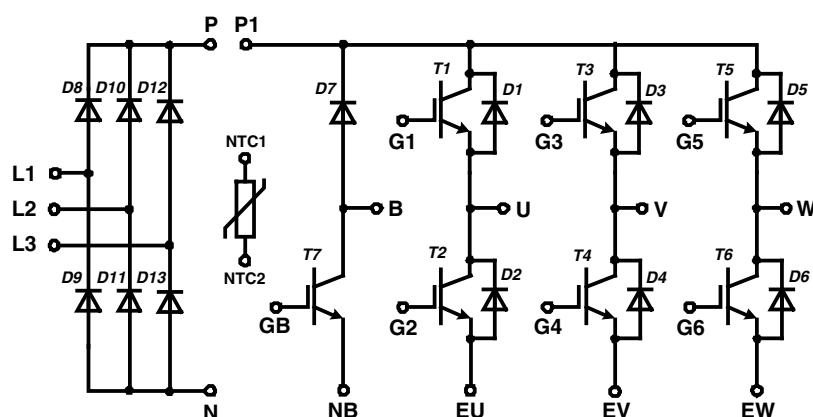
Converter - Brake - Inverter Module

Standard Trench IGBT_T

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAVM25} = 90 \text{ A}$	$I_{C25} = 17 \text{ A}$	$I_{C25} = 17 \text{ A}$
$I_{FSM} = 300 \text{ A}$	$V_{CE(sat)} = 1.9 \text{ V}$	$V_{CE(sat)} = 1.9 \text{ V}$

Part name (Marking on product)

MITA10WB1200TMH



E 72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with standard trench IGBTs
 - very low saturation voltage
 - positive temperature coefficient
 - short tail current
- Epitaxial free wheeling diodes with hiperfast soft reverse recovery
- Temperature sense included

Application:

- AC motor drives
- Pumps, Fans
- Washing machines
- Air-conditioning system
- Inverter and power supplies

Package:

- "Mini" package
- Assembly height is 17 mm
- Insulated base plate
- Pins suitable for wave soldering and PCB mounting
- Assembly clips available
 - IXKU 5-505 screw clamp
 - IXRB 5-506 click clamp
- UL registered E72873

Output Inverter T1 - T6

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V _{CES}	collector emitter voltage	T _{VJ} = 150°C			1200	V	
V _{GES}	max. DC gate voltage	continuous			±20	V	
V _{GEM}	max. transient collector gate voltage	transient			±30	V	
I _{C25}	collector current	T _C = 25°C			17	A	
I _{C80}		T _C = 80°C			12	A	
P _{tot}	total power dissipation	T _C = 25°C			70	W	
V _{CE(sat)}	collector emitter saturation voltage	I _C = 10 A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C	1.9 2.3	2.2	V V	
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.3 A; V _{GE} = V _{CE}	T _{VJ} = 25°C	5	5.5	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C		0.8	0.6	mA mA
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V			150	nA	
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		600		pF	
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 10 A		54		nC	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 100 Ω	T _{VJ} = 25°C	55		ns	
t _r	current rise time			30		ns	
t _{d(off)}	turn-off delay time			320		ns	
t _f	current fall time			200		ns	
E _{on}	turn-on energy per pulse			0.9		mJ	
E _{off}	turn-off energy per pulse			0.75		mJ	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 100 Ω	T _{VJ} = 125°C	60		ns	
t _r	current rise time			35		ns	
t _{d(off)}	turn-off delay time			360		ns	
t _f	current fall time			340		ns	
E _{on}	turn-on energy per pulse			1.55		mJ	
E _{off}	turn-off energy per pulse			1.1		mJ	
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G = 100 Ω; I _C = 20 A; T _{VJ} = 125°C	V _{CEK} ≤ V _{CES} - L _S ·di/dt			V	
I _{SC} (SCSOA)	short circuit safe operating area	V _{CE} = 720 V; V _{GE} = ±15 V; R _G = 100 Ω; t _p = 10 μs; non-repetitive	T _{VJ} = 125°C	40		A	
R _{thJC}	thermal resistance junction to case	(per IGBT)			1.9	K/W	
R _{thCH}	thermal resistance case to heatsink			0.65		K/W	

Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	<i>max. repetitive reverse voltage</i>		$T_{VJ} = 150^{\circ}\text{C}$		1200	V
I_{F25}	<i>forward current</i>		$T_C = 25^{\circ}\text{C}$		24	A
I_{F80}			$T_C = 80^{\circ}\text{C}$		16	A
V_F	<i>forward voltage</i>	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.0 1.6	2.4	V V
Q_{rr}	<i>reverse recovery charge</i>	$V_R = 600\text{ V}$ $di_F/dt = -300\text{ A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	1.9		μC
I_{RM}	<i>max. reverse recovery current</i>			12.8		A
t_{rr}	<i>reverse recovery time</i>			335		ns
E_{rec}	<i>reverse recovery energy</i>			0.54		mJ
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			1.6	K/W
R_{thCH}	<i>thermal resistance case to heatsink</i>			0.55		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake T7

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V _{CES}	collector emitter voltage	T _{VJ} = 150°C			1200	V	
V _{GES}	max. DC gate voltage	continuous			±20	V	
V _{GEM}	max. transient collector gate voltage	transient			±30	V	
I _{C25}	collector current	T _C = 25°C			17	A	
I _{C80}		T _C = 80°C			12	A	
P _{tot}	total power dissipation	T _C = 25°C			70	W	
V _{CE(sat)}	collector emitter saturation voltage	I _C = 10 A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C	1.9 2.3	2.2	V V	
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.3 A; V _{GE} = V _{CE}	T _{VJ} = 25°C	5	5.5	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C	0.8	0.6	mA mA	
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V			150	nA	
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		600		pF	
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 10 A		54		nC	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 100 Ω	T _{VJ} = 25°C	55		ns	
t _r	current rise time			30		ns	
t _{d(off)}	turn-off delay time			320		ns	
t _f	current fall time			200		ns	
E _{on}	turn-on energy per pulse			0.9		mJ	
E _{off}	turn-off energy per pulse			0.75		mJ	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 100 Ω	T _{VJ} = 125°C	60		ns	
t _r	current rise time			35		ns	
t _{d(off)}	turn-off delay time			360		ns	
t _f	current fall time			340		ns	
E _{on}	turn-on energy per pulse			1.55		mJ	
E _{off}	turn-off energy per pulse			1.1		mJ	
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G = 100 Ω; I _C = 20 A; T _{VJ} = 125°C	V _{CEK} ≤ V _{CES} - L _S ·di/dt			V	
I _{SC} (SCSOA)	short circuit safe operating area	V _{CE} = 720 V; V _{GE} = ±15 V; R _G = 100 Ω; t _p = 10 μs; non-repetitive	T _{VJ} = 125°C	40		A	
R _{thJC}	thermal resistance junction to case	(per IGBT)			1.9	K/W	
R _{thCH}	thermal resistance case to heatsink			0.65		K/W	

Brake Chopper D7

					Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 150°C			1200	V	
I _{F25}	forward current	T _C = 25°C			15	A	
I _{F80}		T _C = 80°C			10	A	
V _F	forward voltage	I _F = 10 A; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C	2.5 2.0	3.1	V V	
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C	0.2	0.1	mA mA	
Q _{rr}	reverse recovery charge	V _R = 600 V di _F /dt = tbd A/μs I _F = 10 A; V _{GE} = 0 V	T _{VJ} = 125°C	tbd		μC	
I _{RM}	max. reverse recovery current			tbd		A	
t _{rr}	reverse recovery time			tbd		ns	
E _{rec}	reverse recovery energy			tbd		μJ	
R _{thJC}	thermal resistance junction to case	(per diode)			2.5	K/W	
R _{thCH}	thermal resistance case to heatsink			0.85		K/W	

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

IXYS reserves the right to change limits, test conditions and dimensions.

20070611

Input Rectifier Bridge D8 - D11

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1600		V
I_{FAV}	average forward current	sine 180°	$T_C = 80^{\circ}\text{C}$		22		A
I_{DAVM}	max. average DC output current	rect.; $d = 1/3$	$T_C = 80^{\circ}\text{C}$		61		A
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		300 tbd		A A
I^2t	I^2t value for fusing	$t = 10\text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		450 tbd		A^2s A^2s
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		50		W
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.35 1.35	1.6		V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.3	0.01		mA mA
R_{thJC}	thermal resistance junction to case	(per diode)		0.7	2.1		K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)					K/W

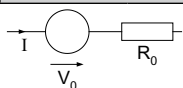
Temperature Sensor NTC

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
R_{25}	resistance	$T_C = 25^{\circ}\text{C}$	4.75	5.0	5.25		k Ω
$B_{25/50}$				3375			K

Module

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
T_{VJ}	operating temperature		-40		125		$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150		$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125		$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500		V~
CTI	comparative tracking index				-		
F_C	mounting force		40		80		N
d_S	creep distance on surface		12.7				mm
d_A	strike distance through air		12				mm
Weight				35			g

Equivalent Circuits for Simulation



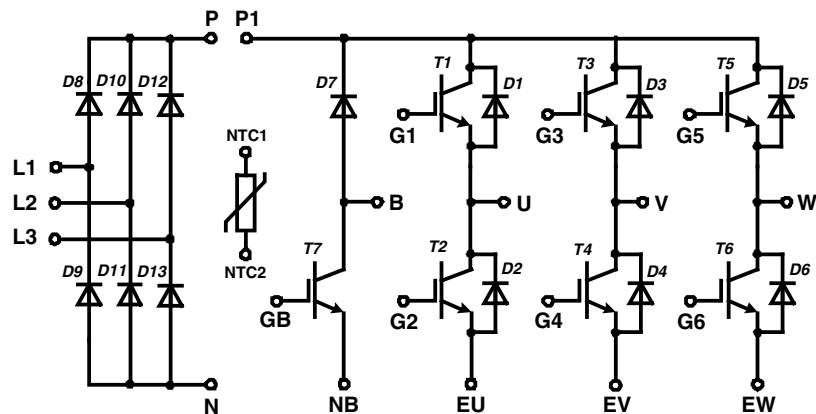
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_0 R_0	rectifier diode	D8 - D13	$T_{VJ} = 125^{\circ}\text{C}$	0.9 16			V m Ω
V_0 R_0	IGBT	T1 - T6	$T_{VJ} = 125^{\circ}\text{C}$	1.0 125			V m Ω
V_0 R_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^{\circ}\text{C}$	1.15 45			V m Ω
V_0 R_0	IGBT	T7	$T_{VJ} = 125^{\circ}\text{C}$	1.0 125			V m Ω
V_0 R_0	free wheeling diode	D7	$T_{VJ} = 125^{\circ}\text{C}$	1.4 60			V m Ω

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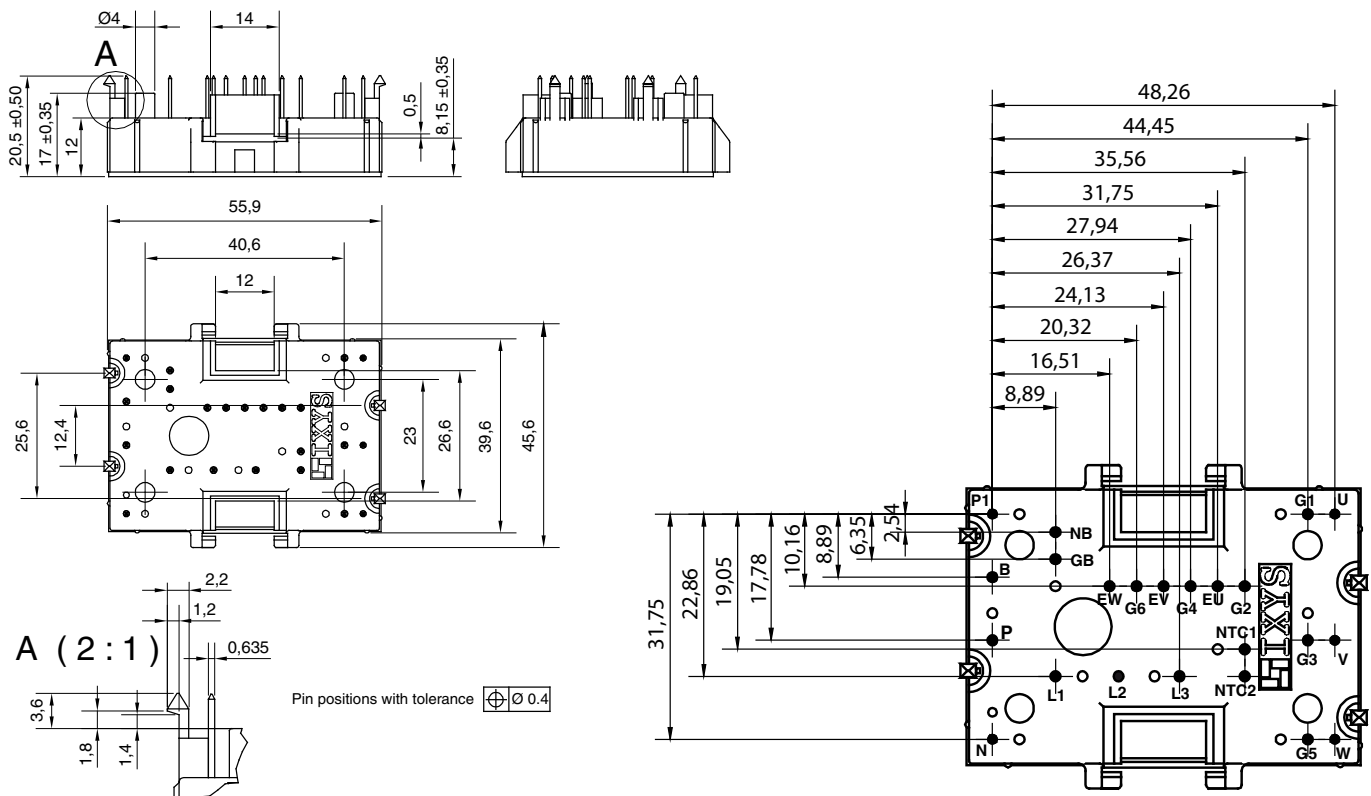
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Circuit Diagram

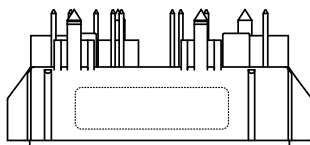


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



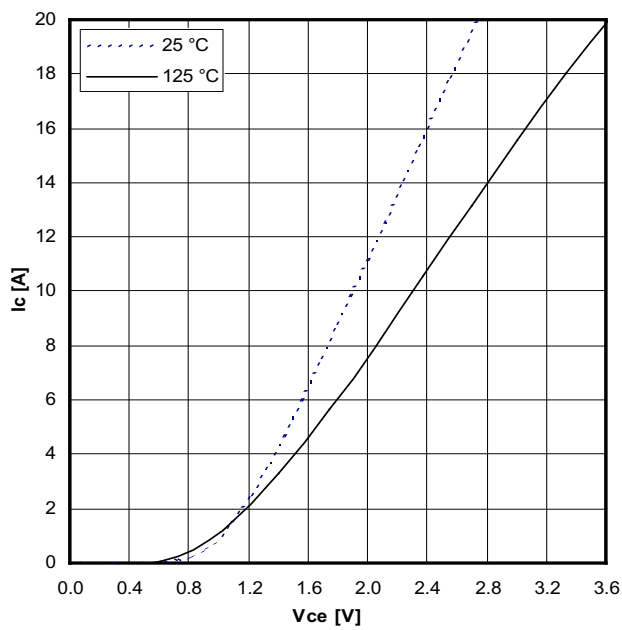
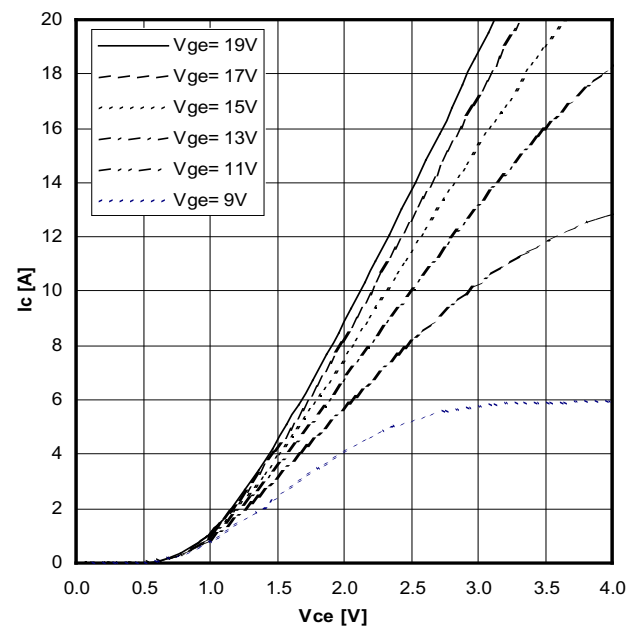
Product Marking



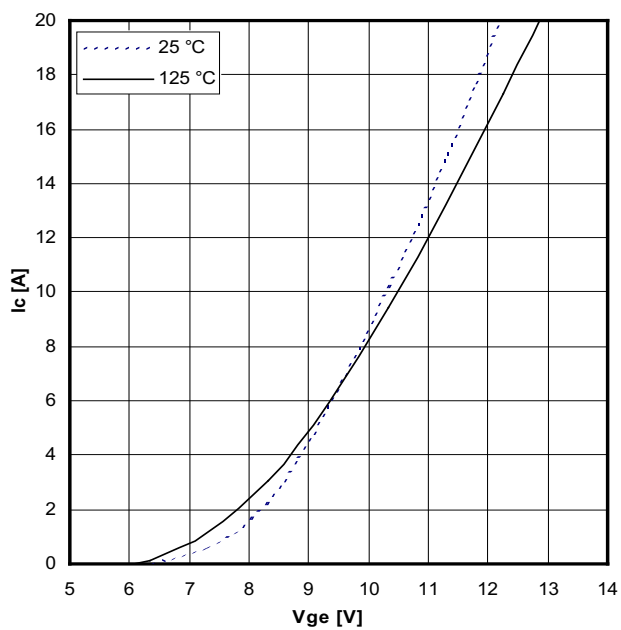
Part number

M = Module
 I = IGBT
 T = Standard trench
 A = Gen 1 / std
 10 = Current Rating [A]
 WB = 6-Pack + 3~ Rectifier Bridge & Brake Unit
 1200 = Reverse Voltage [V]
 T = NTC
 MH = MiniPack2

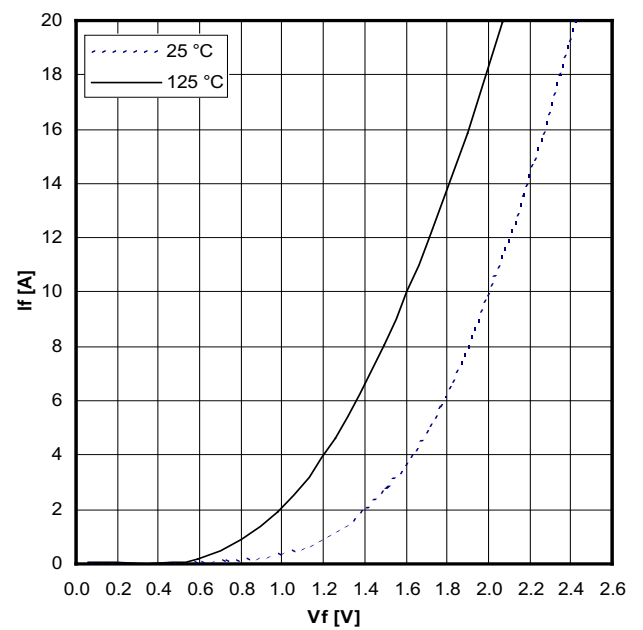
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MITA 10 WB 1200 TMH	MITA10WB1200TMH	Box	20	502214


Typical output characteristics, $V_{GE} = 15\text{ V}$


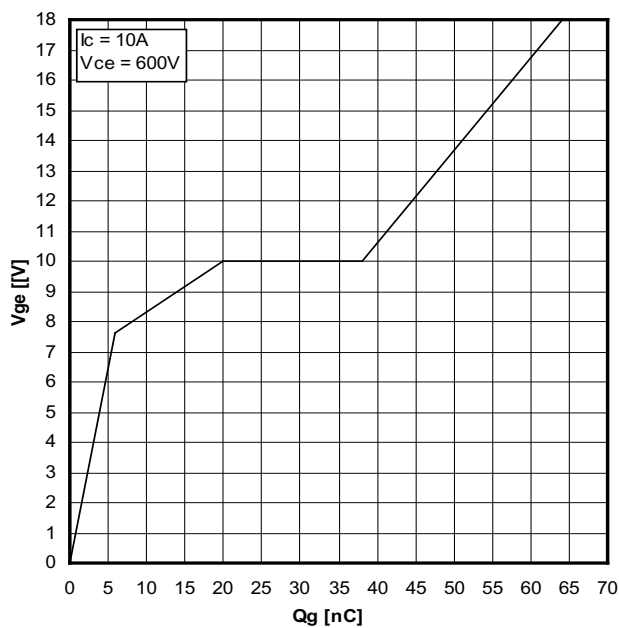
Typical output characteristics (125 °C)



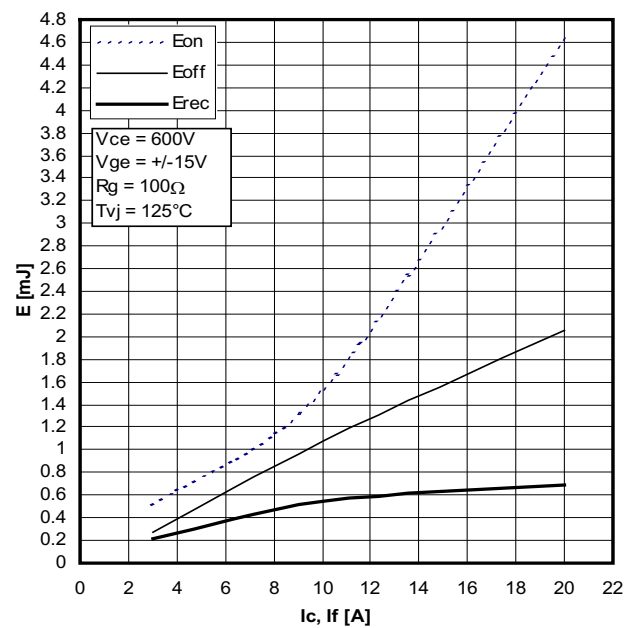
Typical transfer characteristics



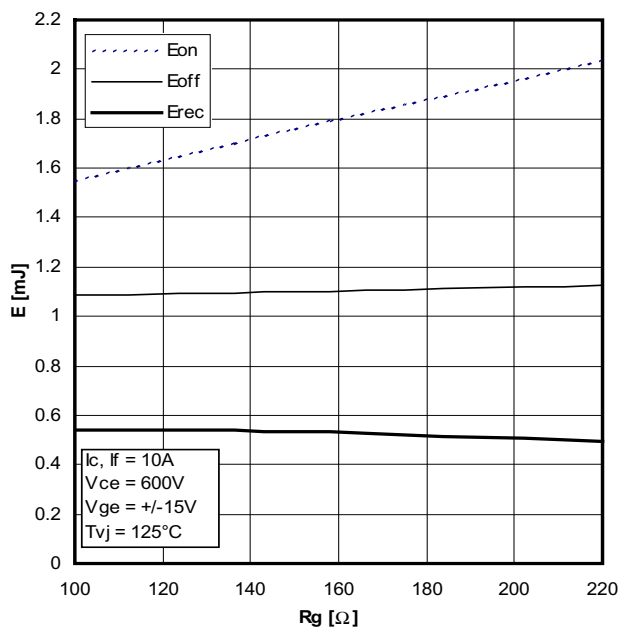
Typical forward characteristics of freewheeling diode



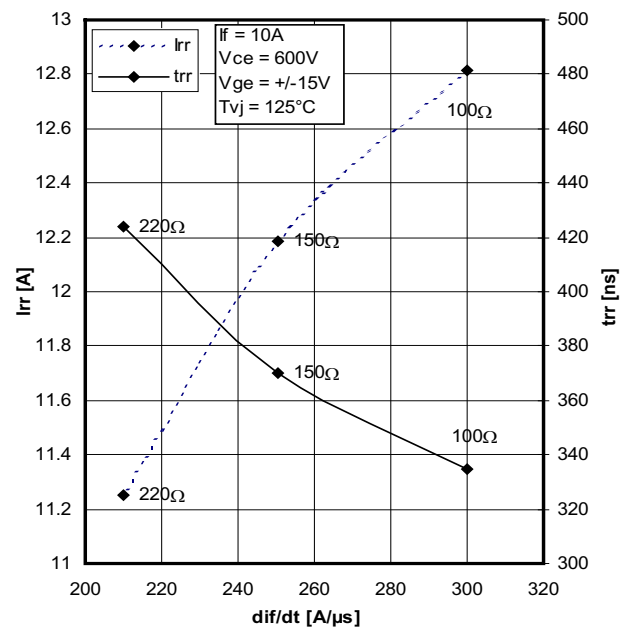
Typical turn on gate charge



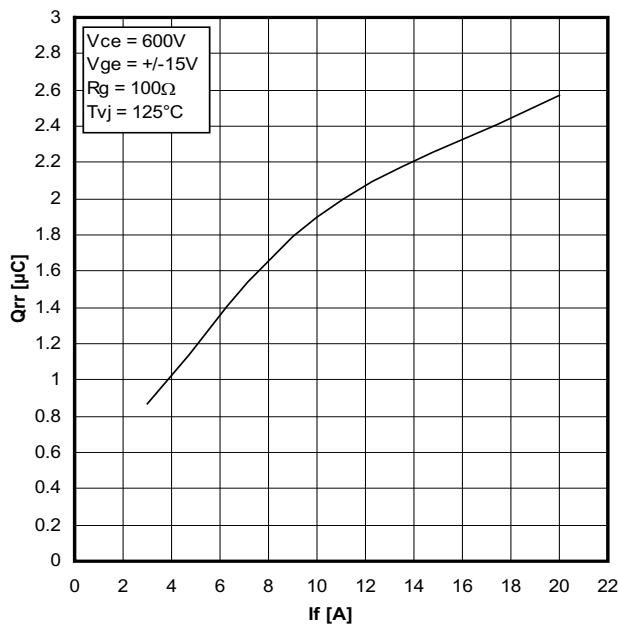
Typical switching energy versus collector current



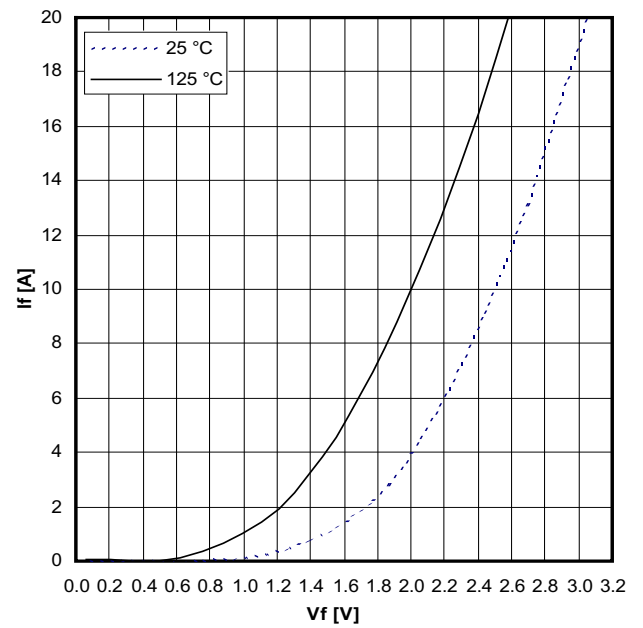
Typical switching energy versus gate resistance



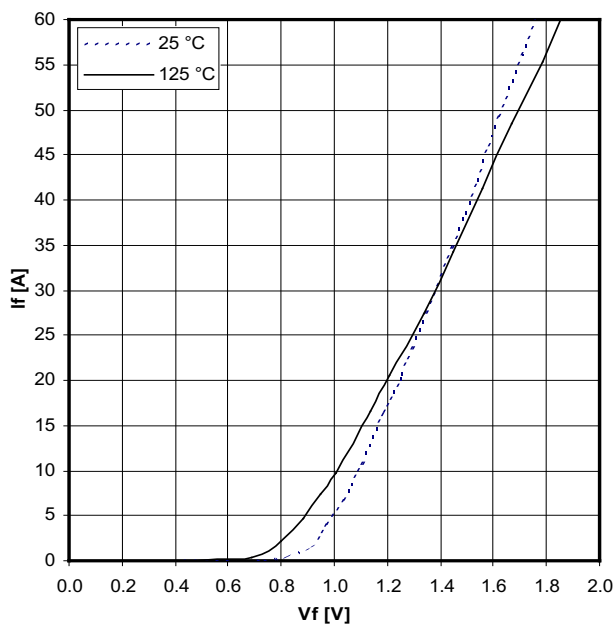
Typical turn-off characteristics of free wheeling diode



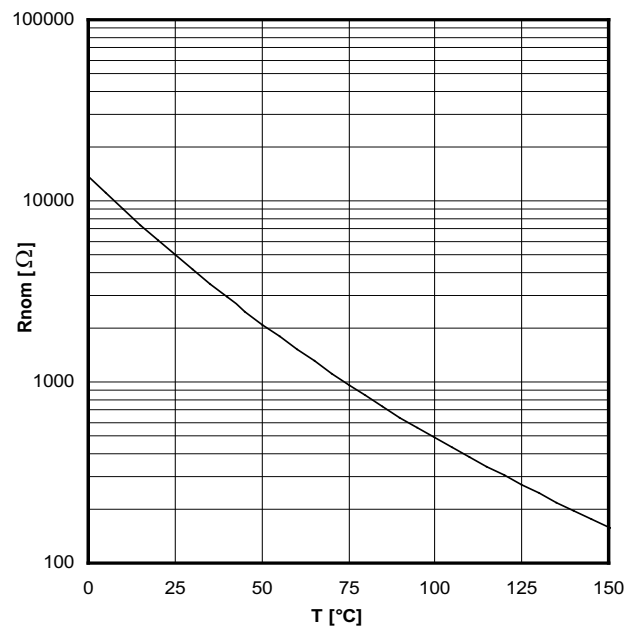
Typical turn-off characteristics of free wheeling diode



Typical forward characteristics of brake diode



Typical forward characteristics per rectifier



Typical thermistor resistance versus temperature